

DHG20I600PA

preliminary

 $V_{RRM} = 600 V$

 $I_{FAV} = 20 A$

 t_{rr} = 40 ns

High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

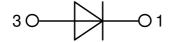
Sonic Fast Recovery Diode

Part number

DHG20I600PA



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
 Vary about reasons times
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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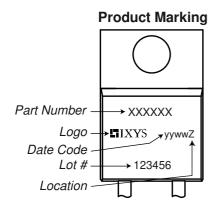
Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blockii	ng voltage	$T_{VJ} = 25^{\circ}C$			600	V
V _{RRM}	max. repetitive reverse blocking vo	oltage	$T_{VJ} = 25^{\circ}C$			600	V
I _R	reverse current, drain current	$V_R = 600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			30	μΑ
		$V_R = 600 \text{ V}$	$T_{VJ} = 125^{\circ}C$			1.5	mA
V _F	forward voltage drop	I _F = 20 A	$T_{VJ} = 25^{\circ}C$			2.25	V
		$I_F = 40 \text{ A}$				3.17	٧
		I _F = 20 A	T _{VJ} = 125°C			2.21	V
		$I_F = 40 \text{ A}$				3.25	٧
I _{FAV}	average forward current	T _C = 95°C	T _{vJ} = 150°C			20	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage		T _{VJ} = 150°C			1.15	V
r _F	slope resistance	ss calculation only				45	mΩ
R _{thJC}	thermal resistance junction to case	;				0.9	K/W
R _{thCH}	thermal resistance case to heatsin	k			0.5		K/W
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			140	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			150	Α
C¹	junction capacitance	$V_R = 400 \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		12		pF
I _{RM}	max. reverse recovery current		T _{VJ} = 25 °C		8		Α
		$I_F = 20 \text{ A}; V_R = 300 \text{ V}$	$T_{VJ} = 125$ °C		12		Α
t _{rr}	reverse recovery time	$\begin{cases} I_F = 20 \text{ A}; V_R = 300 \text{ V} \\ -\text{di}_F / \text{dt} = 450 \text{ A} / \mu \text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}C$		40		ns
)		$T_{VJ} = 125$ °C		60		ns



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Package	TO-220			Rating	s	
Symbol	Definition	Conditions	min	typ.	max.	Unit
I _{RMS}	RMS current	per terminal			35	Α
T _{VJ}	virtual junction temperature		-5	5	150	°C
Top	operation temperature		-5	5	125	°C
T _{stg}	storage temperature		-5	5	150	°C
Weight				2		g
M _D	mounting torque		0.	4	0.6	Nm
F _c	mounting force with clip		2)	60	Ν



Part description

D = Diode

H = Sonic Fast Recovery Diode

G = extreme fast

20 = Current Rating [A]

I = Single Diode 600 = Reverse Voltage [V]

PA = TO-220AC (2)

Or	dering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Sta	andard	DHG20I600PA	DHG20I600PA	Tube	50	504941

Similar Part	Package	Voltage class
DHG20I600HA	TO-247AD (2)	600

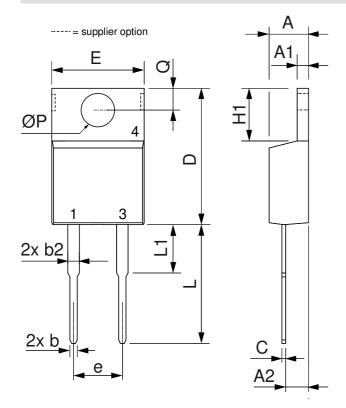
Equivalent Circuits for Simulation		* on die level	$T_{VJ} = 150^{\circ}C$	
$I \rightarrow V_0$	R _o -	Fast Diode		
V _{0 max}	threshold voltage	1.15		V
R _{0 max}	slope resistance *	42		mΩ





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Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
Α	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
С	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
е	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125





Fast Diode

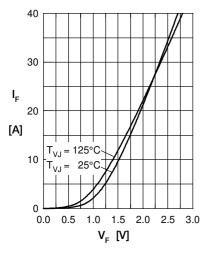


Fig. 1 Typ. Forward current versus V_F

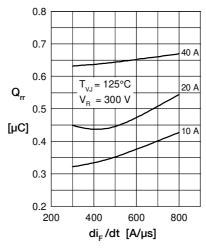


Fig. 2 Typ. reverse recov. charge Q_{rr} versus di/dt

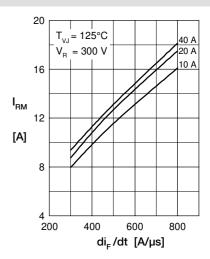


Fig. 3 Typ. peak reverse current I_{RM} versus di/dt

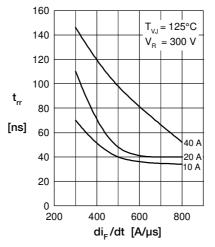
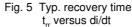
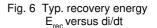


Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}





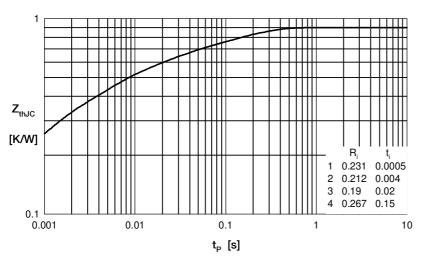


Fig. 7 Typ. transient thermal impedance junction to case

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